

8961726 TEXAS INSTR (OPTO)

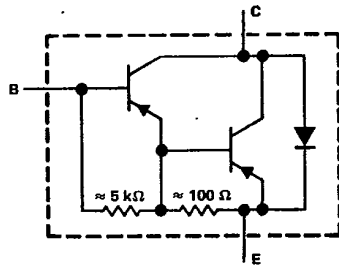
62C 36912 D

TIP135, TIP136, TIP137
P-N-P DARLINGTON
SILICON POWER TRANSISTORS
 REVISED OCTOBER 1984

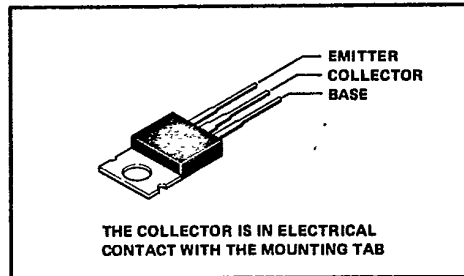
T-33-31

- Designed For Complementary Use With TIP130, TIP131, TIP132
- 70 W at 25°C Case Temperature
- 8 A Rated Collector Current
- Min h_{FE} of 1000 at 4 V, 4 A
- 75 mJ Reverse Energy Rating

device schematic



TO-220AB PACKAGE



absolute maximum ratings at 25°C case temperature (unless otherwise noted)

	TIP135	TIP136	TIP137
Collector-base voltage	-60 V	-80 V	-100 V
Collector-emitter voltage ($I_B = 0$)	-60 V	-80 V	-100 V
Emitter-base voltage	-5 V		
Continuous collector current	-8 A		
Peak collector current (see Note 1)	-12 A		
Continuous base current	-0.3 A		
Safe operating areas at (or below) 25°C case temperature	See Figure 7		
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)	70 W		
Continuous device dissipation at (or below) 25°C free-air temperature (see Note 3)	2 W		
Unclamped inductive load energy (see Note 4)	75 mJ		
Operating collector junction and storage temperature range	-65°C to 150°C		

- NOTES: 1. This value applies for $t_w \leq 0.3$ ms, duty cycle $\leq 10\%$.
 2. Derate linearly to 150°C case temperature at the rate of 0.56 W/°C or refer to Dissipation Derating Curve, Figure 8.
 3. Derate linearly to 150°C free-air temperature at the rate of 20 mW/°C or refer to Dissipation Derating Curve.
 4. This rating is based on the capability of the transistor to operate safely in the circuit in $L = 20$ mH, $R_{BB2} = 100 \Omega$, $V_{BB2} = 0$ V, $R_S = 0.1 \Omega$, $V_{CC} = 20$ V. Energy $\approx I_C^2 L/2$.

5 TIP Devices

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**TIP135, TIP136, TIP137
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SILICON POWER TRANSISTORS**

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TIP135			TIP136			TIP137			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
$V_{(BR)CEO}$	$I_C = -30\text{ mA}$, $I_B = 0$, See Note 5	-60			-80			-100			V
I_{CEO}	$V_{CE} = -30\text{ V}$, $I_B = 0$		-0.5								mA
	$V_{CE} = -40\text{ V}$, $I_B = 0$					-0.5					
	$V_{CE} = -60\text{ V}$, $I_B = 0$							-0.5			
I_{CBO}	$V_{CB} = -60\text{ V}$, $I_E = 0$		-0.2								mA
	$V_{CB} = -80\text{ V}$, $I_E = 0$					-0.2					
	$V_{CB} = -100\text{ V}$, $I_E = 0$							-0.2			
I_{CBO}	$V_{CB} = -60\text{ V}$, $I_E = 0$, $TC = 100^\circ\text{C}$		-0.1								mA
	$V_{CB} = -80\text{ V}$, $I_E = 0$, $TC = 100^\circ\text{C}$					-0.1					
	$V_{CB} = -100\text{ V}$, $I_E = 0$, $TC = 100^\circ\text{C}$							-0.1			
I_{EBO}	$V_{EB} = -5\text{ V}$, $I_C = 0$		-5		-5			-5			mA
h_{FE}	$V_{CE} = -4\text{ V}$, $I_C = -1\text{ A}$, See Notes 5 and 6	500			500			500			
	$V_{CE} = -4\text{ V}$, $I_C = -4\text{ A}$, See Notes 5 and 6	1000	15000		1000	15000		1000	15000		
$V_{CE(sat)}$	$I_B = -16\text{ mA}$, $I_C = -4\text{ A}$, See Notes 5 and 6		-2			-2			-2		V
	$I_B = -30\text{ mA}$, $I_C = -6\text{ A}$, See Notes 5 and 6		-3			-3			-3		
V_{BE}	$V_{CE} = -4\text{ V}$, $I_C = -4\text{ A}$, See Notes 5 and 6		-2.5			-2.5			-2.5		V
C_{obo}	$V_{CB} = -10\text{ V}$, $I_E = 0$		200			200			200		pF
V_F	$I_F = 8\text{ A}$, See Notes 5 and 6		3.5			3.5			3.5		V

- NOTES: 5. These parameters must be measured using pulse techniques, $t_W = 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts located within 3.2 mm (0.125 inch) from the device body.



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TYPICAL CHARACTERISTICS

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STATIC FORWARD CURRENT TRANSFER RATIO
vs
COLLECTOR CURRENT

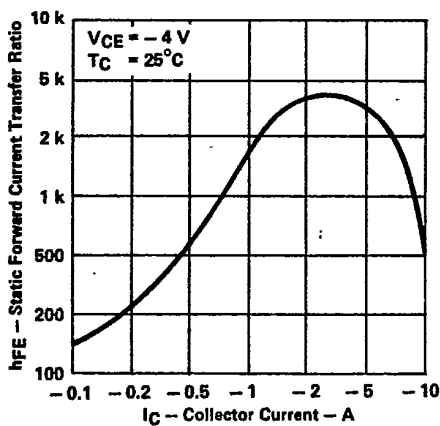


FIGURE 1

COLLECTOR-EMITTER SATURATION VOLTAGE
vs
COLLECTOR CURRENT

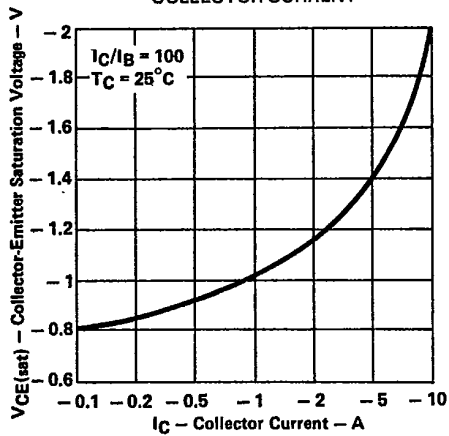


FIGURE 2

BASE-EMITTER VOLTAGE
vs
COLLECTOR CURRENT

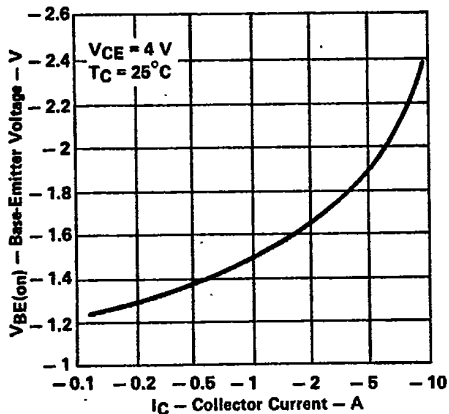


FIGURE 3

FORWARD VOLTAGE OF
COMMUTATING DIODE
vs
FORWARD CURRENT

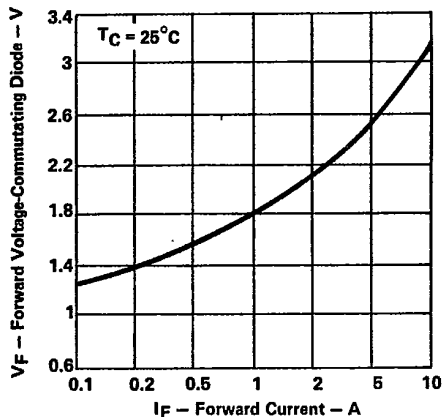


FIGURE 4



TIP Devices

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TYPICAL CHARACTERISTICS

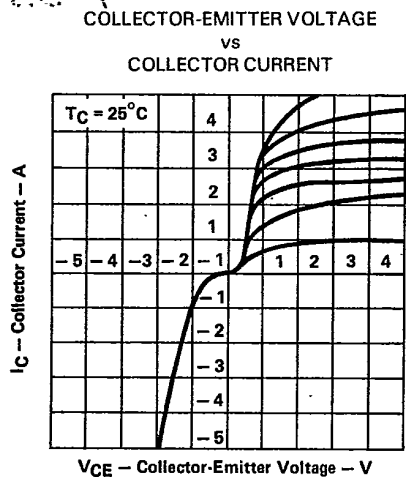


FIGURE 5

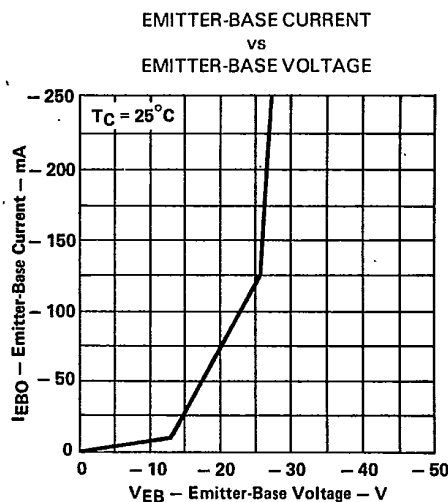


FIGURE 6

MAXIMUM SAFE OPERATING AREA
MAXIMUM COLLECTOR CURRENT
vs
COLLECTOR-EMITTER VOLTAGE

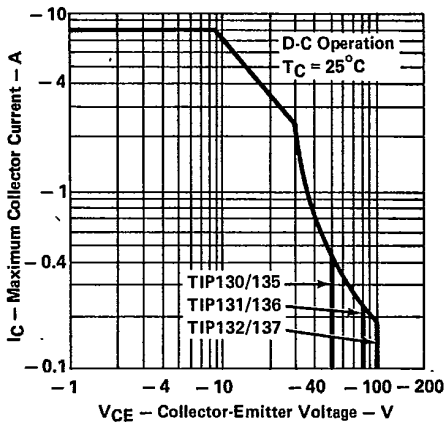


FIGURE 7



TIP Devices

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THERMAL INFORMATION
DISSIPATION DERATING CURVE

T-33-31

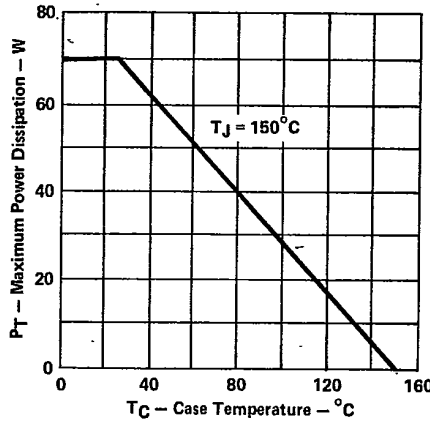


FIGURE 8



TIP Devices